

Vishay Siliconix

# Automotive N-Channel 250 V (D-S) 175 °C MOSFET



Top View G

#### **FEATURES**

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified
- 100 % R<sub>a</sub> and UIS tested

N-Channel MOSFET

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	250				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0300				
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$	0.0320				
I <sub>D</sub> (A)	65				
Configuration	Single				
Package	TO-263				

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unless	s otherwise noted	i)	
PARAMETER	,	SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	250	V
Gate-source voltage	V <sub>GS</sub>	± 20	- V	
Continuous drain current	T <sub>C</sub> = 25 °C	1	65	
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	37	
Continuous source current (diode conduction	on) <sup>a</sup>	I <sub>S</sub>	120	A
Pulsed drain current <sup>b</sup>	I <sub>DM</sub>	180		
Single pulse avalanche current	1 0.1 ml l	I <sub>AS</sub>	41	
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	84	mJ
	T <sub>C</sub> = 25 °C	D	375	w
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	125	]
Operating junction and storage temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount c	$R_{thJA}$	40	°C/W		
Junction-to-case (drain)	-case (drain)		0.4	C/ VV		

#### **Notes**

- b. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						l.		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		250	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	3.0	3.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 250 V	-	-	1	μА	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 250 V, T <sub>J</sub> = 125 °C	-	-	50		
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 250 V, T <sub>J</sub> = 175 °C	-	-	600	<b>1</b>	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0244	0.0300		
Duning any una para state una interna a	Б	V <sub>GS</sub> = 7.5 V	I <sub>D</sub> = 10 A	-	0.0260	0.0320		
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0650	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0868	1	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 15 A	-	50	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	2880	4050	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	1480	2100		
Reverse transfer capacitance	C <sub>rss</sub>	1		-	58	85		
Total gate charge <sup>c</sup>	Qg			-	50	75		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$ $V_{DS} = 125 \text{ V}, I_{D} = 10 \text{ A}$		-	12	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	1	1		15	-		
Gate Resistance	$R_{g}$	f = 1 MHz		1.40	2.84	4.40	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>				14	30		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} =$	125 V, $R_L$ = 12.5 $Ω$	-	6	15	1 _	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 A$ ,	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		38	60	ns	
Fall time <sup>c</sup>	t <sub>f</sub>	1		-	10	20		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	180	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		-	0.82	1.5	V	
Body diode reverse recovery time	t <sub>rr</sub>				155	260	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>	]	-	933	1400	nC		
Reverse recovery fall time	t <sub>a</sub>				122	-	ns	
Reverse recovery rise time	t <sub>b</sub>				33	-		
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>				-11.6	-	Α	

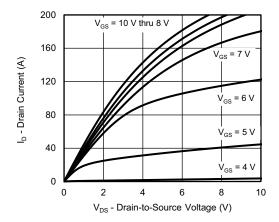
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

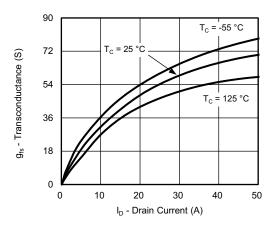
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



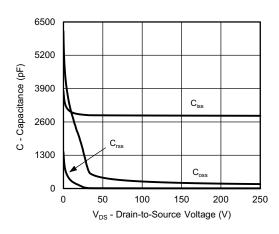
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



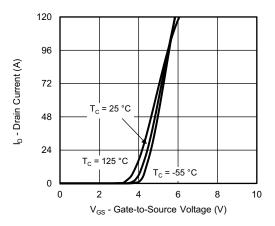
#### **Output Characteristics**



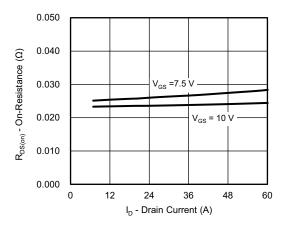
Transconductance



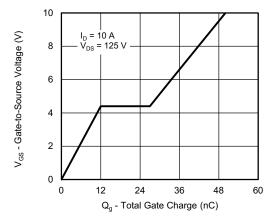
Capacitance



**Transfer Characteristics** 



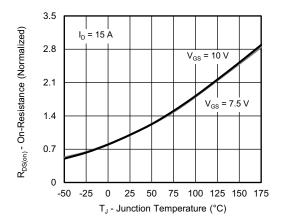
On-Resistance vs. Drain Current



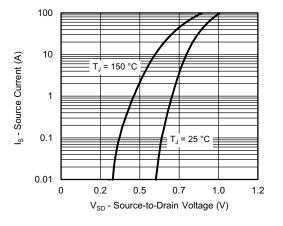
**Gate Charge** 



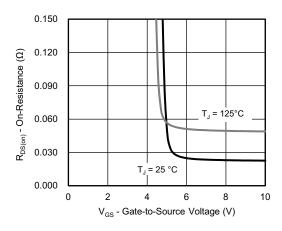
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



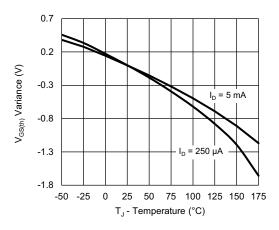
On-Resistance vs. Junction Temperature



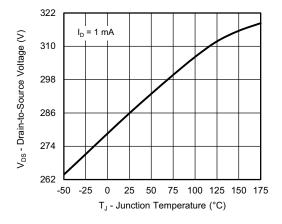
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



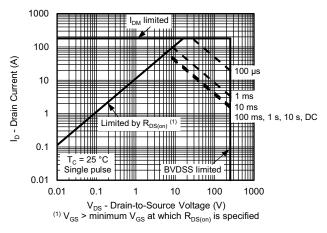
**Threshold Voltage** 



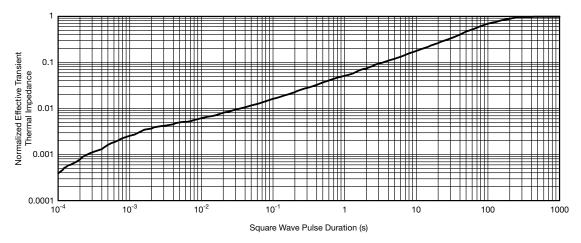
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



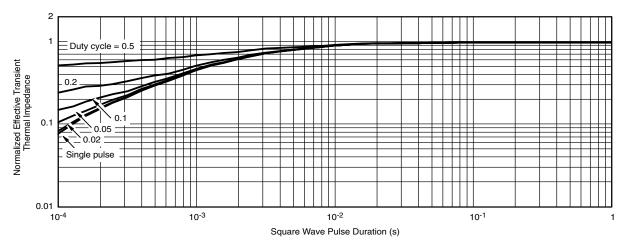
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions

- Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

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# TO-263 (D<sup>2</sup>PAK): 3-LEAD









DETAIL A (ROTATED 90°)



⋝:	,	 	b— b1–		ļ	ļ
2:	П				5	ပ
	SE	СТ	ION	ΙΔ.	- 1 - Δ	Ŧ

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. \*: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

		INCHES		MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4		0.010 BSC		BSC	
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





## RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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